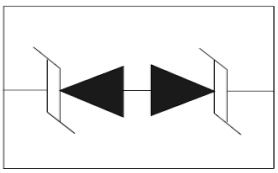
Descriptions

The ESD5451N is a bi-directional TVS (Transient Voltage Suppressor). It is specifically designed to protect sensitive
electronic components which are connected to low speed data lines and control lines from over-stress caused by ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and Lightning.

The ESD5451N may be used to provide ESD protection up to ±30kV (contact and air discharge) according to IEC61000-4-2, and withstand peak pulse current up to 8A (8/20μs) according to IEC61000-4-5.

The ESD5451N is available in DFN1006-2L package. Standard products are Pb-free and Halogen-free.



Features

- Reverse stand-off voltage: ±5V Max
- Transient protection for each line according to
  IEC61000-4-2 (ESD): ±30kV (contact and air discharge)
  IEC61000-4-4 (EFT): 40A (5/50ns)
  IEC61000-4-5 (surge): 8A (8/20μs)
- Capacitance: C_J = 17.5pF typ.
- Low leakage current: I_R < 1nA typ.
- Low clamping voltage: V_{CL} = 9V typ. @ I_{PP} = 16A (TLP)
- Solid-state silicon technology

Applications

- Cellular handsets
- Tablets
- Laptops
- Other portable devices
- Network communication devices

Absolute maximum ratings

Parameter	Symbol	Rating	Unit
Peak pulse power (t_p = 8/20μs)	P_{pk}	80	W
Peak pulse current (t_p = 8/20μs)	I_{PP}	8	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	±30	kV
ESD according to IEC61000-4-2 contact discharge		±30	
Operation junction temperature	T_J	125	°C
Lead temperature	T_L	260	°C
Storage temperature	T_{STG}	-55~150	°C

Electrical characteristics (T_A=25°C, unless otherwise noted)

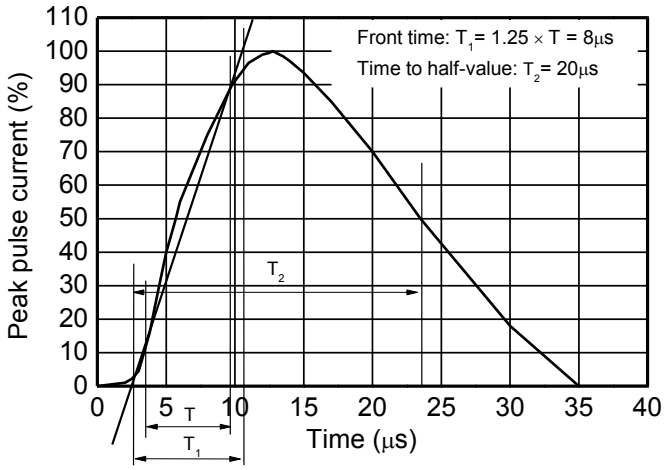
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				±5	V
Reverse leakage current	I_R	V_{RWM} = 5V		<1	100	nA
Reverse breakdown voltage	V_{BR}	I_{BR} = 1mA	5.1			V
Reverse holding voltage	V_{HOLD}	I_{HOLD} = 50mA	5.1			V
Clamping voltage 1)	V_{CL}	I_{PP} = 16A, t_p = 100ns		9		V
Clamping voltage 2)	V_{CL}	V_{ESD} = 8kV		9		V
Clamping voltage 3)	V_{CL}	I_{PP} = 1A, t_p = 8/20μs			6.5	V
		I_{PP} = 5A, t_p = 8/20μs			8.5	V
		I_{PP} = 8A, t_p = 8/20μs			10	V
Dynamic resistance 1)	R_{DYN}			0.20		Ω
Junction capacitance	C_J	V_R = 0V, f = 1MHz		17.5	22	pF
		V_R = 5V, f = 1MHz		11.5	16	pF

1) TLP parameter: Z_0 = 50Ω , t_p = 100ns, t_r = 2ns, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.

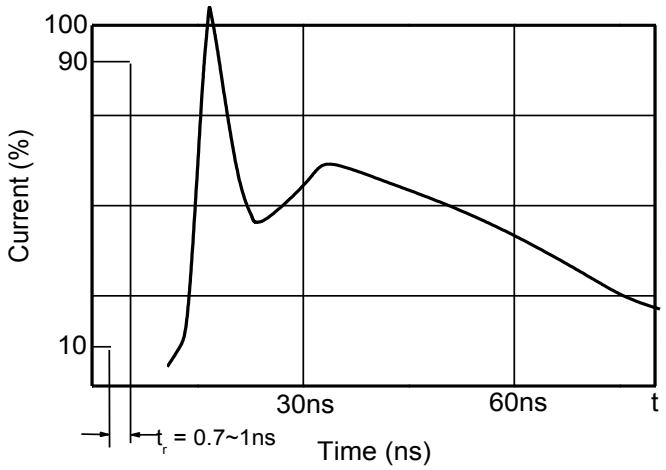
2) Contact discharge mode, according to IEC61000-4-2.

3) Non-repetitive current pulse, according to IEC61000-4-5.

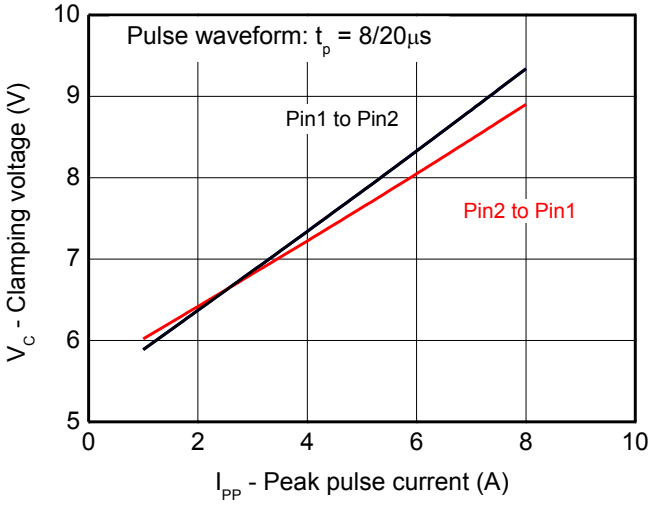
Typical characteristics (T_A=25°C, unless otherwise noted)



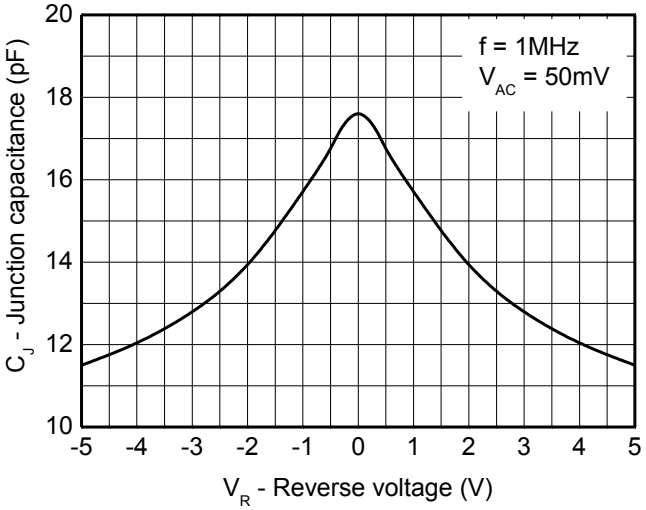
8/20μs waveform per IEC61000-4-5



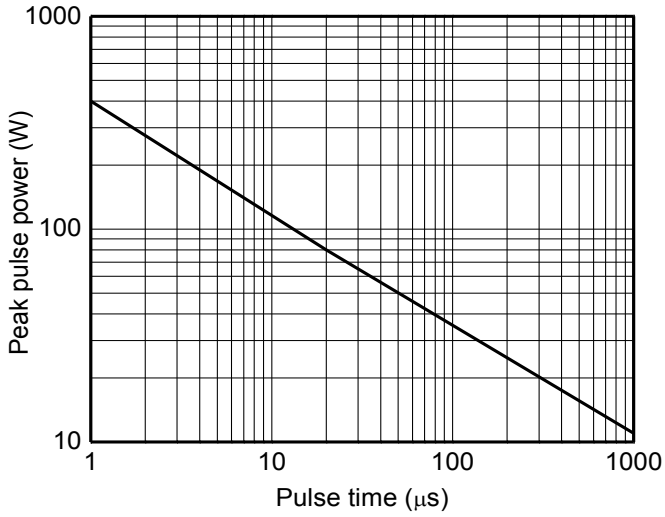
Contact discharge current waveform per IEC61000-4-2



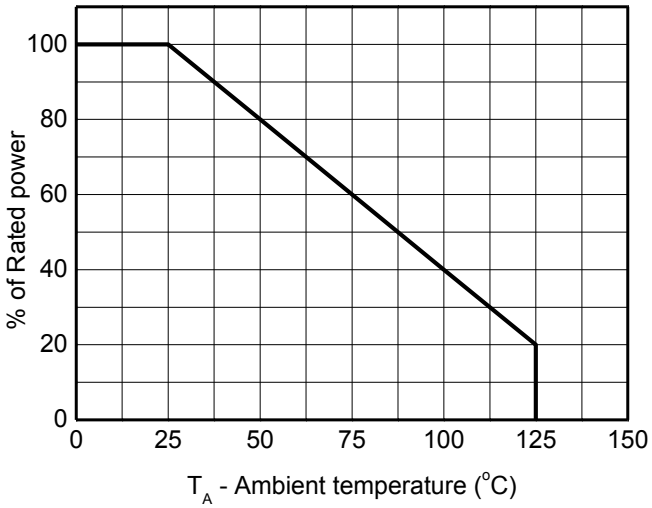
Clamping voltage vs. Peak pulse current



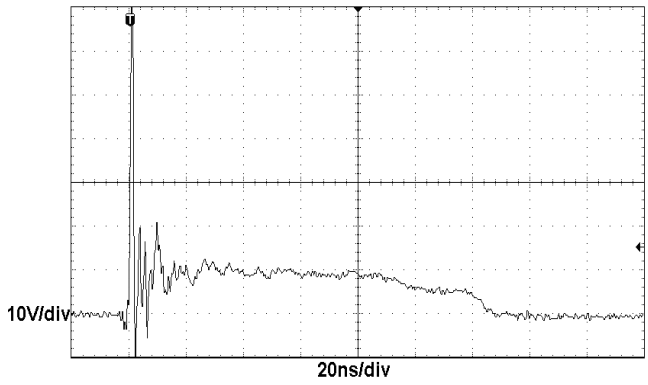
Capacitance vs. Reveres voltage



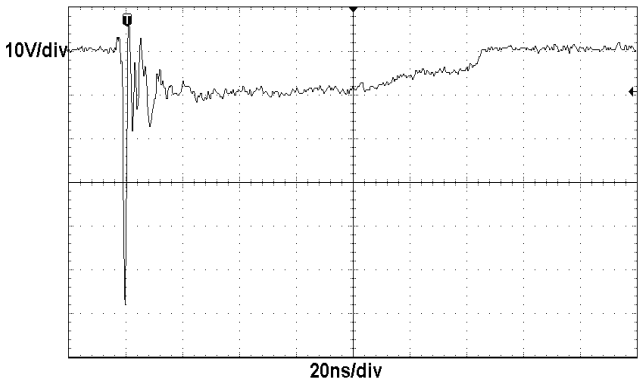
Non-repetitive peak pulse power vs. Pulse time



Power derating vs. Ambient temperature



ESD clamping
(+8kV contact discharge per IEC61000-4-2)



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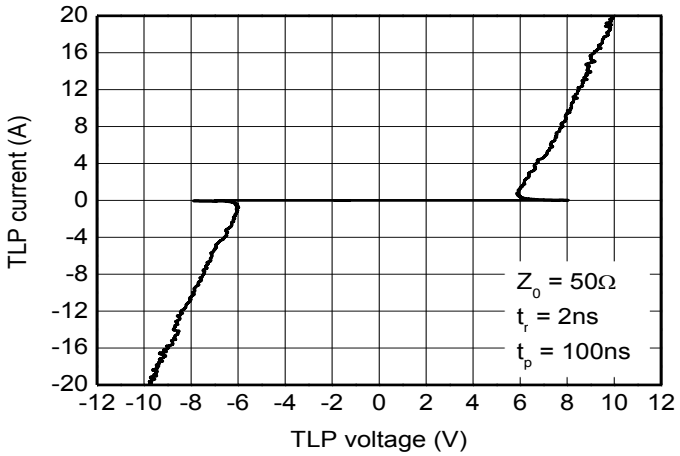
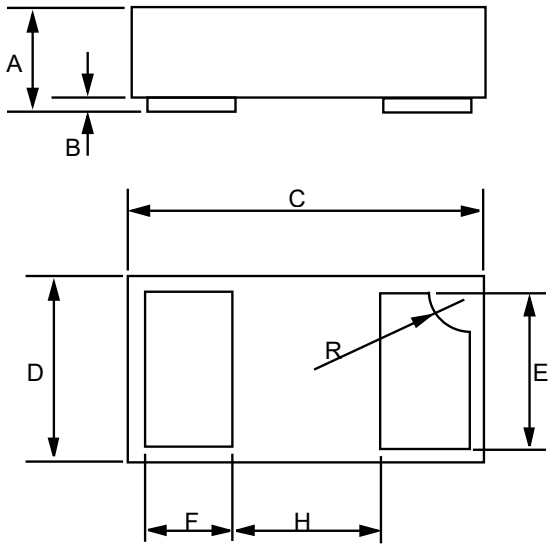


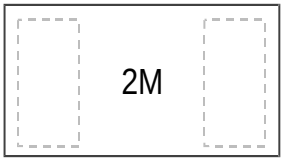
TLP Measurement

DFN1006-2 PACKAGE OUTLINE DIMENSIONS



Dim	Inches		Millimeters	
	MIN	MAX	MIN	MAX
A	0.013	0.020	0.34	0.50
B	0.000	0.002	0.00	0.05
C	0.037	0.042	0.95	1.075
D	0.021	0.026	0.55	0.675
E	0.017	0.021	0.45	0.55
F	0.007	0.011	0.20	0.30
H	0.015Typ.		0.40Typ.	
R	0.001	0.005	0.05	0.15

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
ESD5451N	DFN1006-2	10000	Tape and reel